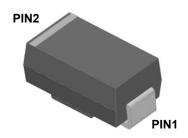




Silicon Carbide Schottky Diode

V_{RRM}	650V
I _{F(135°C)}	2.4A
Q _c	8.3nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: DO-214AC (SMA)
- Terminals: Tin plated leads
- Polarity: Cathode line denotes the cathode end

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			A1
Reverse voltage (Repetitive peak) @ T _i =25°C	V_{RRM}	٧	650
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	650
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	650
Continuous forward current @ T _C =25°C			5.5
Continuous forward current @ T _C =135°C	I _F	А	2.4
Continuous forward current @ T _C =163°C			1
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	Α	18
Repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FRM}	Α	10
Power Dissipation@ T _C =25°C	Б	W	16.4
Power Dissipation@ T _C =110°C	Ртот		7.1
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	1.62
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



■Electrical Characteristics (T_C=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min.	Тур.	Max.
Reverse voltage (DC)	V_{DC}	V	I _R =0.25mA, T _j =25°C	850	-	-
Forward voltage V _F		V	I _F =1A, T _j =25°C	-	1.13	1.30
	V	I _F =1A, T _j =175°C	-	1.20	-	
Davidence or wheel		μА	V _R =650V, T _j =25°C	-	0.02	0.5
Reverse current I _R	IR		V _R =650V, T _j =175°C	-	0.1	-
Total capacitive charge	Q _C	nC	V_R =400V, T_j =25°C Q_C = $\int_0^{VR}C(V)dV$	-	8.3	-
Total capacitance C		V _R =0V, f=1MHZ	-	142	-	
	С	pF	V _R =200V, f=1MHZ	-	15.7	-
			V _R =400V, f=1MHZ	-	15.3	-
Capacitance stored energy	Ec	μJ	V _R =400V	-	1.3	-

■Thermal Characteristics

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance, junction to case	$R_{\theta J\text{-}C}$	°C M/	9.12
Thermal resistance, junction to ambient	$R_{\theta J-A}$	°C W	90

■Typical Characteristics (Typical)

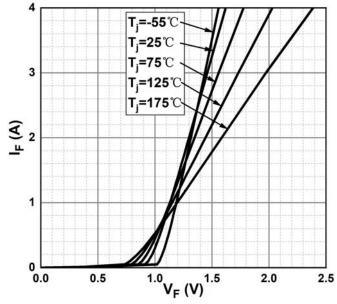


Figure 1. Forward Characteristics

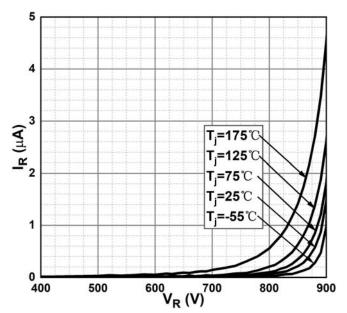
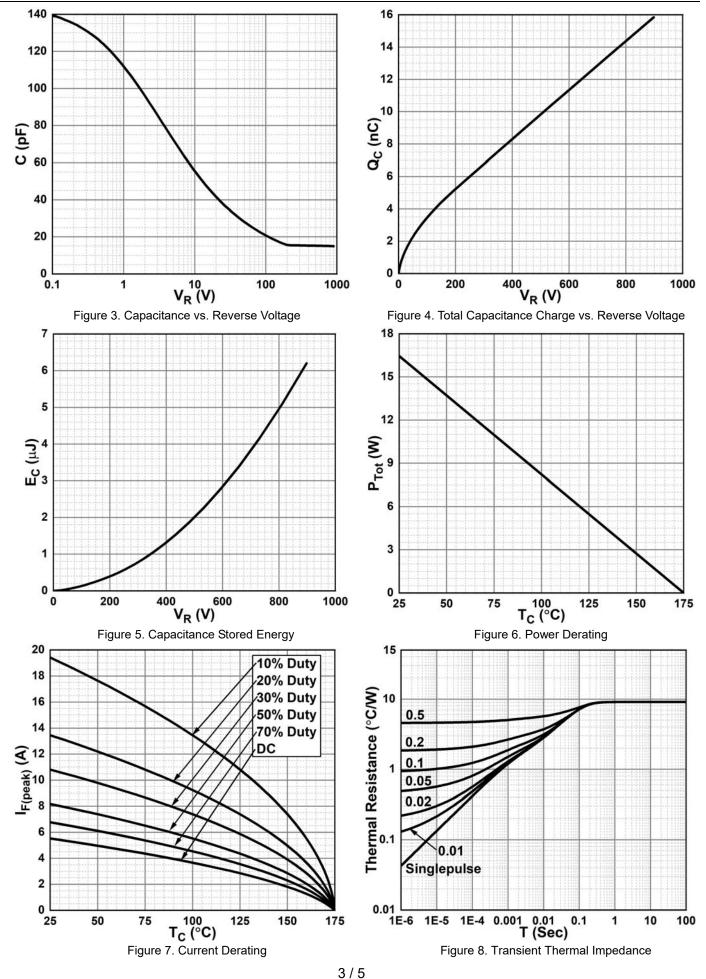


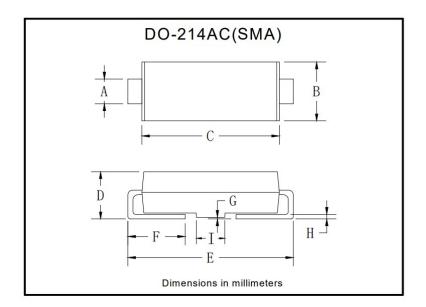
Figure 2. Reverse Characteristics





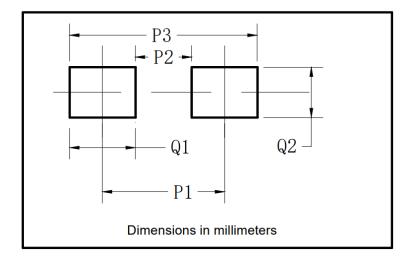


■Outline Dimensions



DO-214AC(SMA)		
Dim	Min	Max
Α	1.25	1.58
В	2.40	2.83
С	4.00	4.75
D	1.90	2.30
E	4.93	5.28
F	0.76	1.41
G	0.05	0.20
Н	0.15	0.31
Ī	1.70	2.10

■Suggested Pad Layout



DO-214AC(SMA)		
Dim	Millimeters	
P1	4.00	
P2	1.50	
P3	6.50	
Q1	2.50	
Q2	1.70	



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